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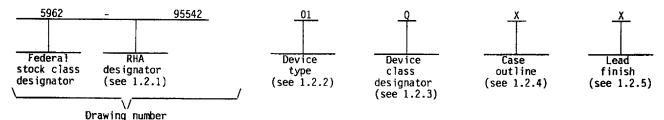
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<u>DISTRIBUTION STATEMENT A</u>. Approved for public release; distribution is unlimited.

5962-E066-95

1. SCOPE

- 1.1 <u>Scope</u>. This drawing forms a part of a one part one part number documentation system (see 6.6 herein). Two product assurance classes consisting of military high reliability (device classes Q and M) and space application (device class V), and a choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). Device class M microcircuits represent non-JAN class B microcircuits in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices". When available, a choice of Radiation Hardness Assurance (RHA) levels are reflected in the PIN.
 - 1.2 PIN. The PIN shall be as shown in the following example:



- 1.2.1 RHA designator. Device class M RHA marked devices shall meet the MIL-I-38535 appendix A specified RHA levels and shall be marked with the appropriate RHA designator. Device classes Q and V RHA marked devices shall meet the MIL-I-38535 specified RHA levels and shall be marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.
 - 1.2.2 Device type(s). The device type(s) shall identify the circuit function as follows:

Device type Generic number Circuit function

O1 DS3886 BTL 9-bit latching data transceiver

1.2.3 <u>Device class designator</u>. The device class designator shall be a single letter identifying the product assurance level as follows:

Device class

Device requirements documentation

М

Vendor self-certification to the requirements for non-JAN class B microcircuits in accordance with 1.2.1 of MIL-STD-883

0 or V

Certification and qualification to MIL-I-38535

1.2.4 <u>Case outline(s)</u>. The case outline(s) shall be as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	<u>Terminals</u>	<u>Package style</u>
X	See figure 1	48	flat package

1.2.5 <u>Lead finish</u>. The lead finish shall be as specified in MIL-STD-883 (see 3.1 herein) for class M or MIL-I-38535 for classes Q and V. Finish letter "X" shall not be marked on the microcircuit or its packaging. The "X" designation is for use in specifications when lead finishes A, B, and C are considered acceptable and interchangeable without preference.

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1.3 Absolute maximum ratings. 1/ Driver input and receiver output - - - - - - - - - -5.5 V 2.4 V ±15 mA -65°C to +150°C 1.7 W +260°C +175°C See MIL-STD-1835 87 C/W 1.4 Recommended operating conditions. +4.5 V dc to +5.5 V 1.5 <u>Digital logic testing for device classes Q and V.</u> Fault coverage measurement of manufacturing logic tests (MIL-STD-883, test method 5012) - - - - - 3/ XX percent APPLICABLE DOCUMENTS 2.1 Government specification, standards, bulletin, and handbook. Unless otherwise specified, the following specification, standards, bulletin, and handbook of the issue listed in that issue of the Department of Defense Index of Specifications and Standards specified in the solicitation, form a part of this drawing to the extent specified herein. SPECIFICATION MILITARY MIL-I-38535 - Integrated Circuits, Manufacturing, General Specification for. STANDARDS MILITARY Test Methods and Procedures for Microelectronics. Configuration Management. MIL-STD-883 MIL-STD-973 MIL-STD-1835 - Microcircuit Case Outlines. BULLETIN MILITARY MIL-BUL-103 - List of Standardized Military Drawings (SMD's). HANDBOOK MILITARY MIL-HDBK-780 - Standardized Military Drawings. (Copies of the specification, standards, bulletin, and handbook required by manufacturers in connection with specific acquisition functions should be obtained from the contracting activity or as directed by the contracting activity.) Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability. Derate at 11.5 mW/ C above +25 C. Values will be added when they become available. 5962-95542 SIZE STANDARD MICROCIRCUIT DRAWING A DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444 REVISION LEVEL SHEET 3 DESC FORM 193A

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2.2 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing shall take precedence.

3. REQUIREMENTS

- 3.1 Item requirements. The individual item requirements for device class M shall be in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices" and as specified herein. The individual item requirements for device classes Q and V shall be in accordance with MIL-I-38535, and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not effect the form, fit, or function as described herein.
- 3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-STD-883 (see 3.1 herein) for device class M and MIL-I-38535 for device classes Q and V and herein.
 - 3.2.1 <u>Case outline(s)</u>. The case outline(s) shall be in accordance with 1.2.4 herein and figure 1.
 - 3.2.2 <u>Terminal connections</u>. The terminal connections shall be as specified on figure 2.
 - 3.2.3 <u>Truth table</u>. The truth table shall be as specified on figure 3.
 - 3.2.4 Logic diagram. The logic diagram shall be as specified on figure 4.
- 3.2.5 <u>Test circuits and switching waveforms</u>. The test circuits and switching waveforms shall be as specified on figure 5.
- 3.3 <u>Electrical performance characteristics and postirradiation parameter limits</u>. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full case operating temperature range.
- 3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are defined in table I.
- 3.5 Marking. The part shall be marked with the PIN listed in 1.2 herein. Marking for device class M shall be in accordance with MIL-STD-883 (see 3.1 herein). In addition, the manufacturer's PIN may also be marked as listed in MIL-BUL-103. Marking for device classes Q and V shall be in accordance with MIL-I-38535.
- 3.5.1 <u>Certification/compliance mark</u>. The compliance mark for device class M shall be a "C" as required in MIL-STD-883 (see 3.1 herein). The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-I-38535.
- 3.6 <u>Certificate of compliance</u>. For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-BUL-103 (see 6.7.2 herein). For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.7.1 herein). The certificate of compliance submitted to DESC-EC prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device class M, the requirements of MIL-SID-883 (see 3.1 herein), or for device classes Q and V, the requirements of MIL-I-38535 and the requirements herein.
- 3.7 <u>Certificate of conformance</u>. A certificate of conformance as required for device class M in MIL-STD-883 (see 3.1 herein) or for device classes Q and V in MIL-I-38535 shall be provided with each lot of microcircuits delivered to this drawing.
- 3.8 <u>Notification of change for device class M.</u> For device class M, notification to DESC-EC of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change as defined in MIL-STD-973.
- 3.9 <u>Verification and review for device class M.</u> For device class M. DESC. DESC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.
- 3.10 <u>Microcircuit group assignment for device class M</u>. Device class M devices covered by this drawing shall be in microcircuit group number 100 (see MIL-I-38535, appendix A).
 - 4. QUALITY ASSURANCE PROVISIONS
- 4.1 <u>Sampling and inspection</u>. For device class M, sampling and inspection procedures shall be in accordance with MIL-STD-883 (see 3.1 herein). For device classes Q and V, sampling and inspection procedures shall be in accordance7 with MIL-I-38535 or as modified in the device manufacturer's QM plan. The modification in the QM plan shall not effect the form, fit, or function as described herein.

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Test	Symbol	Conditions ~55°C ≤ To ≤ +1%	25°C	Group A subgroups	Device type	Limits		Unit
		$-55^{\circ}C \le T_{C} \le +12$ $V_{CC} = 5^{\circ}V + 12$ unless otherwise spe	ecified	Juby. Gupt		Min	Max	
Oriver and control inputs:	(CD, T/R,	An, ACLK, LE and RBYP)					
Logical 1 input voltage	VIH			1, 2, 3	01	2		V
Logical O input voltage	VIL			1, 2, 3	01		0.8	V
Input leakage current	II	V _{CC} = 5.5 V. V _{IN} =	5.5 V	1, 2, 3	01		100	μА
Input high current	IIH	V _{CC} = 5.5 V. V _{IN} = An = CD = 0.5 V. T/R = 2.4 V	2.4 V	1, 2, 3	01		40	μΑ
Input low current	IIL	V _{CC} = 5.5 V, V _{IN} = An = CD = 0.5 T/R = 2.4 V	V	1, 2, 3	01		-100	μΑ
Input diode clamp voltage	v _{IC}	V _{CC} = 4.5 V, I _{CLAMP}	= -12 mA	1, 2, 3	01		-1.2	V
Driver output/receiver inpu	t: (Bn)	,						
Output low bus voltage	V _{OLB}	V _{CC} = 4.5 V, I _{OL} =		1, 2	01	0.75	1.10	٧
		CD = 0.5 V , An = T/\overline{R} = 2.4 V	<u>1</u> /	3		0.75	1.15	
Output low bus current	IOLBZ	$V_{CC} = 5.5 \text{ V, An} = 0.75 \text{ T/R} = 2.4 \text{ V}$.5 V V.	1, 2, 3	01		-100	μА
Output high bus current	^I онвz	V _{CC} = 5.5 V, An = 6 CD = 0 V, BN = 2.1 T/R = 2.4 V).5 V, V,	1, 2, 3	01		100	μА
Receiver input threshold	v _{TH}	$T/\overline{R} = CD = 0.5 V$		1, 2, 3	01	1.47	1.62	V
See footnotes at end of tab	le.							
STA MICROCIRO DEFENSE ELECTRO			SIZ A	E			596	52-9554
DAYTON,		444		RI	EVISION	LEVEL	SHEE	ET 5

Test	Symbol	Conditions -55°C ≤ To ≤ +125°C	Group A subgroups	Device type	Limits		Unit
		$-55^{\circ}\text{C} \le T_{\text{C}} \le +125^{\circ}\text{C}$ $V_{\text{CC}} = 5^{\circ}\text{V} + 10^{\circ}\text{c}$ unless otherwise specified			Min	Max	
Positive clamp diode voltage	VCLP	V _{CC} = 5.5 or 0 V, IBn = 1 mA	1, 2, 3	01	2.0	4.6	٧
		V _{CC} = 5.5 or 0 V, IBn = 10 mA	1, 2, 3		2.6	5.1	
Negative clamp diode voltage	V _{CLN}	V _{CC} = 5.5 V, I _{clamp} = -12 mA	1, 2, 3	01		-1.2	V
Receiver output: (AN)							
Logical 1 output voltage	v _{OH}	$V_{CC} = 4.5 \text{ V, Bn} = 1.1 \text{ V}$ $I_{OH} = -2 \text{ mA, } T/\overline{R} = \text{CD} = 0.5 \text{ V}$	1, 2, 3	01	2.4		٧
Logical O output voltage	VOL	$V_{CC} = 4.5 \text{ V. Bn} = 2.1 \text{ V}$ $I_{OL} = 8 \text{ mA.} T/R = \text{CD} = 0.5 \text{ V}$	1, 2, 3	01		0.4	٧
		$V_{CC} = 4.5 \text{ V}, \text{ Bn} = 2.1 \text{ V}$ $I_{OL} = 24 \text{ mA}, \text{ T/R} = \text{CD} = 0.5 \text{ V}$				0.5	
TRI-STATE leakage current	I _{OZ}	$V_{CC} = 5.5 \text{ V}, CD = 2.4 \text{ V}, BNC = 0.75 \text{ V}, V_{IN} = 2.4 \text{ V}, T/\overline{R} = 0.5 \text{ V}$	1, 2, 3	01		40	μΑ
		V _{CC} = 5.5 V, CD = 2.4 V, BN = 0.75 V, V _{IN} = 0.5 V, T/R = 0.5 V				-100	
Output short circuit current	Ios	$V_{CC} = 5.5 \text{ V}, \text{ Bn} = 1.1 \text{ V},$ $T/\overline{R} = CD = 0.5 \text{ V}$ $\underline{2}/$	1, 2, 3	01	-40	-100	mA
Functional test		V _{CC} = 4.5 V to 5.5 V See 4.4.1b	7,8				
See footnotes at end of table	2.						

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MICROCIRCUIT DRAWING
DEFENSE ELECTRONICS SUPPLY CENTER
DAYTON, OHIO 45444

SIZE
A

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Test	Symbol	Conditions -55°C ≤ T _C ≤ +12	25°C s	Group A subgroups	Device type	L ir	nits	Unit
		$V_{CC} = 5 \text{ V} \pm 10\%$ unless otherwise spe	ecified		Min	Max		
Supply current						,		
Supply current includes V _{CC}	¹ сст	$V_{CC} = 5.5 \text{ V, CD} = 0.5$ T/R=An=ACLK=RBYP=LE=		1, 2, 3	01		70	mA
Supply current for a TTL high input	1 _{CC}	$T/\overline{R} = CD = 0.5 \text{ V}, Ba$ ACLK = RBYP = LE = 0.5 ACL	n = 2.1V 0.5 V	1, 2, 3	01		60	mA
Live insertion current	ILI	$V_{CC} = 5.5 \text{ V}$, $T/\overline{R} = \text{An} = \text{CD} = \text{ACLK}$	= 0.5 V	1, 2, 3	01		6	mA
		$V_{CC} = 5.5 \text{ V, CD} = A$ $T/\overline{R} = AN = RBYP = 2$	1				3	
Driver					• •			
An to Bn propagation delay fall-through mode	^t PHLA	CD = 0 V, Rt = 12.5 RBYP = T/R = 3 V C _L = 30 pF	ohms	9, 10, 1	1 01	1	8	ns
An to Bn propagation delay fall-through mode	^t PLHA	CD = 0 V, RL = 12.5 T/R = RBYP = 3 V C _L = 30 pF	ohms	9, 10, 1	1 01	1	8	ns
ACLK to Bn propagation delay latch mode	^t PHLCK	CD = RBYP = 0 V, $T/\overline{R} = 3 V, RL = 12.$ $C_L = 30 pF$	5 ohms	9, 10, 1	1 01	1	9	ns
ACLK to Bn propagation delay latch mode	^t PLHCK	CD = RBYP = 0 V, $T/\overline{R} = 3 V, RL = 12.$ $C_L = 30 pF$.5 ohms	9, 10, 1	1 01	1	8	ns
CD to Bn enable time	†PHLCD	An = 3 V, $T/R = 3$ V C _L = 30 pF, RL = 12	/, 2.5 ohms	9, 10,	1 01	2	12	ns
CD to Bn disable time	^t PLHCD	An = 3 V, T/\overline{R} = 3 V C _L = 30 pF, RL = 12	V. 2.5 ohms	9, 10,	01	2	9	ns
T/R to Bn enable time	t _{PHLTR}	CD = 0 V, RBYP = 3	V	9, 10,	01	8	25	ns
T/R to Bn: disable time	t _{PLHTR}	CD = 0 V, RBYP = 3	V	9, 10,	01	3	12	ns
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MICROCIRCUIT DRAWING DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		A		REVISION LEVEL			SHEET	

Test	Symbol	Conditi -55°C ≤ To ≤	ons +125°C	Group A	Device type	Li	mits	Unit
		$-55^{\circ}\text{C} \leq \text{I}_{\text{CC}} \leq \text{V}_{\text{CC}} = 5^{\circ}\text{V} \pm \text{unless otherwise}$	10% specified			Min	Max	
Driver (continued)							,	
Transition time 20% to 80%	t _r	CD = RBYP = 0 V, CL = 30 pF, RL =	$T/\overline{R} = 3 \text{ V},$ 12.5 ohms	9, 10, 11	01	1	4	ns
Transition time 80% to 20%	t _f	CD = RBYP = 0 V, CL = 30 pF, RL =	$T/\overline{R} = 3 \text{ V},$ 12.5 ohms	9, 10, 11	01	1	4	ns
Slew rate	S _R	from 1.3 to 1.8 CD = RBYP = 0 V,	V 1/₹ = 3 V	9, 10, 11	01	1		. ns
Skew between drivers in the same package	t _{skewD}	An to Bn		9, 10, 11	01		5	ns
the same package	ACLK to Bn						5	
Driver timing requirements								
An to ACLK setup time	t _{sD}	,		9, 10, 11	01		3	ns
An to ACLK hold time	t _{hD}			9, 10, 11	01		3	ns
ACLK pulse width	tpwD		-	9, 10, 11	01		3	ns
Receiver	· I.							
Bn to An propagation delay bypass mode	t _{PHLB}	LE = 3 V, CD = T C _L = 50 pF, Rt =	/R = 0 V 1K ohms	9, 10, 11	01	2	9	ns
Bn to An propagation delay bypass mode	^t PLHB	LE = 3 V, CD = T C _L = 30 pF	/R = 0 V	9, 10, 11	01	2	9	ns
LE to An propagation delay latch mode	^t PHLLE	CD = T/R = 0 V, C _L = 50 pF	RL = 1 K	9, 10, 11	01	3	11	ns
LE to An propagation delay latch mode	^t PLHLE	$CD = T/\overline{R} = 0 \text{ V},$ $C_L = 50 \text{ pF}$		9, 10, 11	01	3	11	ns
See footnotes at end of tabl	e.				, L			
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Test	Symbol	Conditions -55°C < To ≤ +125°C	Group A	Device type	Limits		Unit
		-55° C \leq T _C \leq +125°C V _{CC} = 5 \forall \pm 10% unless otherwise specified			Min	Max	
Receiver (continued)					· · · · · · · · · · · · · · · · · · ·		
CD to An disable time	t _{PLZCD}	$LE = 3 \text{ V, } Bn = 2.1 \text{ V,} \\ T/\overline{R} = 0 \text{ V, } RL = 500 \text{ ohms,} \\ C_L = 50 \text{ pF}$	9, 10, 11	01	1	18	ns
CD to An enable time	t _{PZLCD}	$LE = 3 \text{ V}, 8n = 2.1 \text{ V}, \\ T/\overline{R} = 0 \text{ V}, RL = 500 \text{ ohms}, \\ C_L = 50 \text{ pF}$	9, 10, 11	01	3	13	ns
CD to An disable time	t _{PHZCD}	LE = 3 V, Bn = 1.1 V, $T/\overline{R} = 0 \text{ V, RL} = 500 \text{ ohms,}$ $C_L = 50 \text{ pF}$	9, 10, 11	01	3	11	ns
CD to An enable time	^t PZHCD	$Bn = 1.1 \text{ V},$ $T/R = 0 \text{ V}, RL = 500 \text{ ohms},$ $C_L = 50 \text{ pF}$	9, 10, 11	01	3	11	ns
T/R to An disable time	t _{PLZTR}	LE = 3 V, CD = 0 V	9, 10, 11	01	3	18	ns
T/R to An enable time	t _{PZLTR}	LE = 3 V, CD = 0 V	9, 10, 11	01	3	18	กร
Disable time	t _{PHZTR}	LE = 3 V, CD = 0 V Bn = 1.1 V, RL = 500 ohms C _L = 50 pF	9, 10, 11	01	3	11	ns
T/R to An enable time	t _{PZHTR}	LE = 3 V, CD = 0 V Bn = 1.1 V, RL = 500 ohms C _L = 50 pF	9, 10, 11	01	3	11	ns
Skew between receivers in the same package	^t skewR	Bn to An <u>3/</u> LE to An	9, 10, 11	01		5	ns

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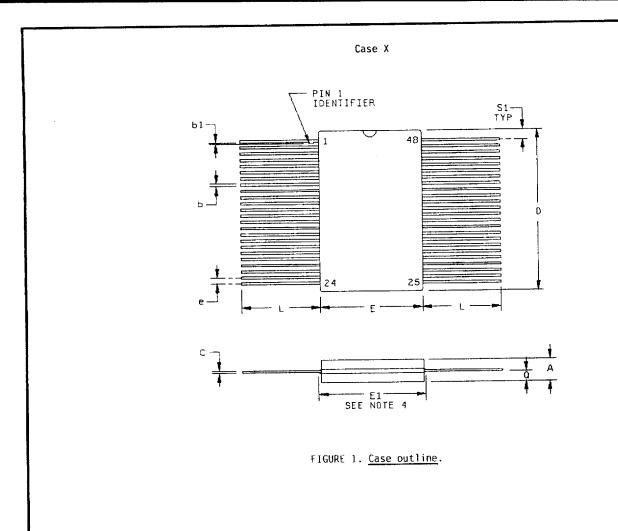
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Test	Symbol Symbol	Conditions	Group A subgroups	Device type	Limits		Unit
	V _{CC} = 5 V + 10%		Min	Max			
Receiver timing requireme	ents						
Bn to LE setup time	t _{sBn}	CD = T/R = 0 V	9, 10, 11	01		3	ns
LE to Bn hold time	t _{hLE}	$CD = T/\overline{R} = 0 V$	9, 10, 11	01		3	ns
LE pulse width	t _{pwLE}	$CD = T/\overline{R} = 0 V$	9, 10, 11	01		3	ns

 ^{1/} Referenced to appropriate signal ground. Do not exceed maximum power dissipation of package.
 2/ Only one output at a time should be shorted and duration of short not to exceed one second.
 3/ tskew is an absolute value defined as differences seen in propagation delays between drivers/receivers in the same pacakge.

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	Millin	neters	Inches		Notes	
Dimensions	Min	Max	Min	Max		
А	1.78	2.54	.070	.100		
b	0.20	0.30	.008	.012		
b1	0.08	0.18	.003	.007		
с	0.10	0.23	.004	.009		
d		16.26		-640		
е	0.64	BSC	.025	BSC		
E	9.55	9.75	.376	.384		
E1		10.16		.400	4	
L	6.35	8.89	.250	.350		
Q	0.79	1.14	.031	.045	5	
S1	0.13		.005			

NOTES:

- 1. The preferred unit of measurement is millimeters. However, this item was designed using inch-pound units of measurements. In case of problems involving conflicts between the metric and inch-pound units, the inch-pound units shall rule.
- 2. Lead number 1 is identified by a tab located on the lead.
- 3. Lead numbers are shown for reference only and do not appear on package.
 4. Dimensions E1 allow for glass meniscus.
- 5. Dimension Q shall be measured at the point of exit of the lead from the body.

FIGURE 1. Case outline. - continued

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Device type	All	Device type	All
Case outline	X	Case outline	X
Terminal number	Terminal symbol	Terminal number	Terminal symbol
1	NC NC	25	, NC
2	LI	26	NC
3	NC	27	RBYP
4	Q GND	28	ACLK
5	LE	29	B8 GND
6	v _{cc}	30	В8
7	AO	31	В7
8	NC	32	B7 GND
9	A1	33	B6 GND
10	A2	34	B6
11	A3	35	B5
12	GND	36	B5 GND
13	A4	37	B4 GND
14	Q V _{CC}	38	B4
15	v _{cc}	39	В3
16	A5	40	B3 GND
17	A6	41	B2 GND
18	A7	42	NC
19	A8	43	B2
20	T/R	44	B1
21	CD	45	B1 GND
22	GND	46	80 GND
23	NC	47	80
24	NC	48	NC

FIGURE 2. <u>Terminal connections</u>.

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· · · · · · · · · · · · · · · · · · ·		_	0.000	A C1 1/	An	Bn*
CD	T/R	LE	RBYP	ACLK	An	
н	Х	X	Х	X	Z	н
L	н	Х	Н	х	L	Н
L	н	Х	Н	х	Н	Ĺ
L	Н	Х	L	x	Х	Bn _o
L	Н	Х	L	L-H	Н	L
L	Н	Х	L	L-H	Ĺ	Н
L	L	н	Х	х	Н	L
L	L	Н	Х	х	L	H
L	L	L	х	х	An _o	X

* = Assumed to be pulled up to 2.1 V.
X = High or low logic state.
Z = High impedance state.

L = Low state.

H = High state.
L-H = Low to high transition.

An = No change from previous state.

Bn = No change from previous state.

For BTL, high and low state is nominally 2.1 V and 1.0 V, respectively.

For BTL, high and low state is nominally 2.4 V and 0.5 V, respectively.

FIGURE 3. Truth table.

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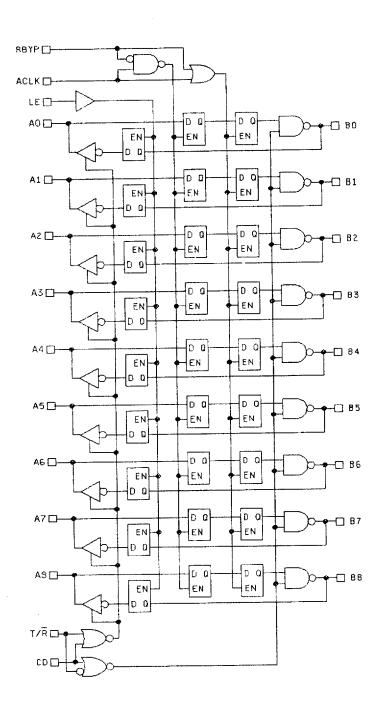
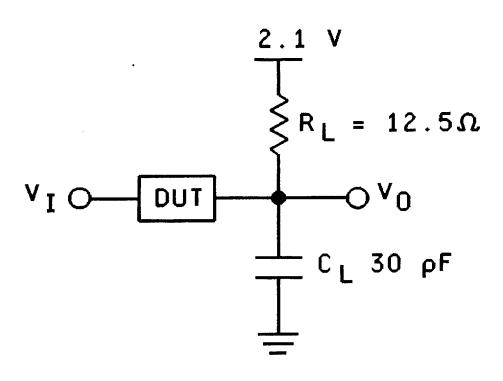
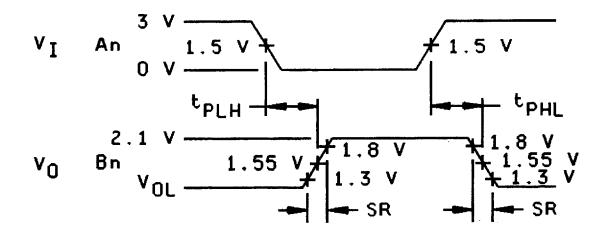


FIGURE 4. Logic diagram.

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Driver propagation delay set-up



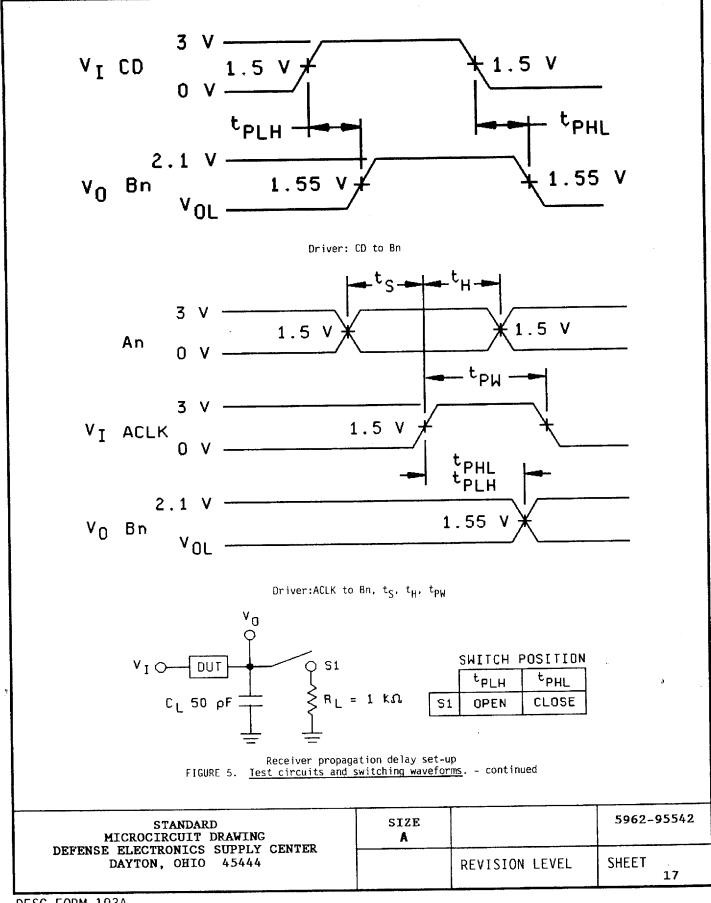
Driver: An to Bn, SR

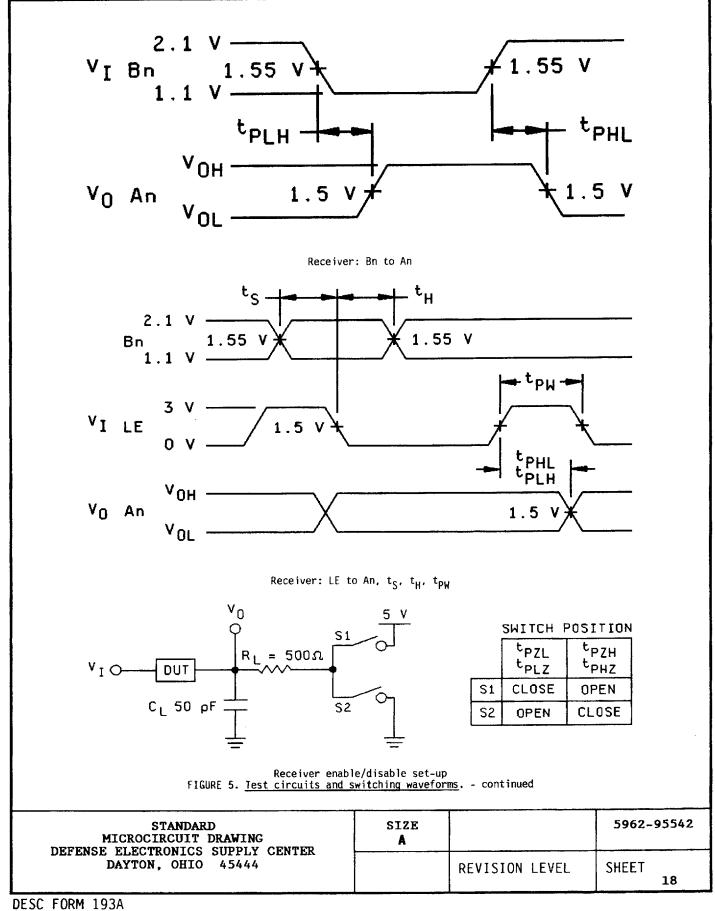
FIGURE 5. Test circuits and switching waveforms.

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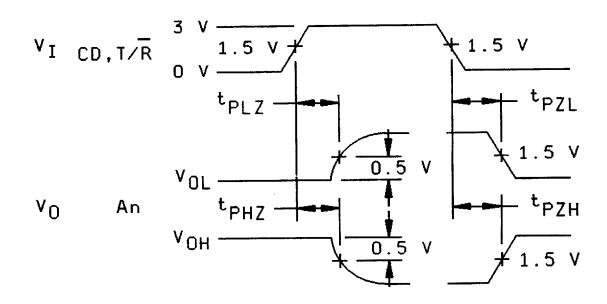
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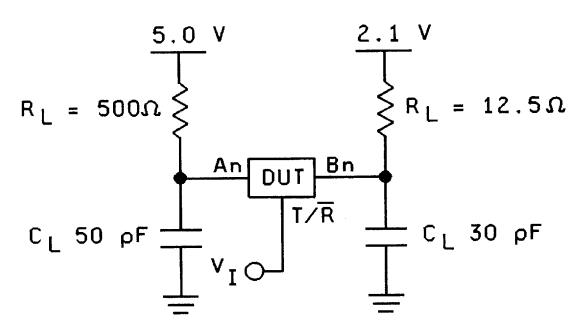




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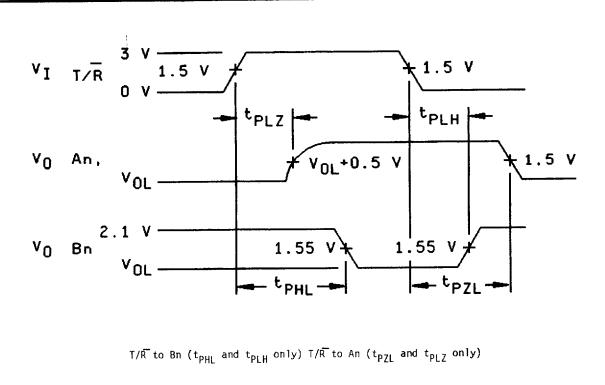
Receiver: CD to An, $\mbox{T/R}$ to An ($\mbox{t}_{\mbox{PHZ}}$ and $\mbox{t}_{\mbox{PZH}}$ only)



T/R to An, T/R to Bn

FIGURE 5. Test circuits and switching waveforms. - continued

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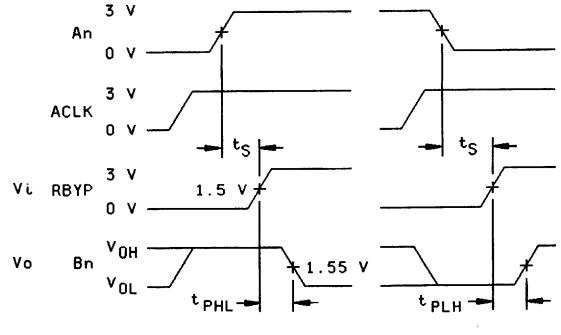


FIGURE 5. Test circuits and switching waveforms. - continued

RBYP to Bn

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- 4.2 <u>Screening</u>. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. For device classes Q and V, screening shall be in accordance with MIL-I-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection.
 - 4.2.1 Additional criteria for device class M.
 - a. Burn-in test, method 1015 of MIL-STD-883.
 - (1) Test condition A, B, C or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
 - (2) $T_A = +125$ °C, minimum.
 - b. Interim and final electrical test parameters shall be as specified in table II herein.
 - 4.2.2 Additional criteria for device classes Q and V.
 - a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-1-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-1-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
 - b. Interim and final electrical test parameters shall be as specified in table II herein.
 - c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in appendix B of MIL-I-38535.
- 4.3 Qualification inspection for device classes Q and V. Qualification inspection for device classes Q and V shall be in accordance with MIL-I-38535. Inspections to be performed shall be those specified in MIL-I-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).
- 4.4 <u>Conformance inspection</u>. Quality conformance inspection for device class M shall be in accordance with MIL-STD-883 (see 3.1 herein) and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4). Technology conformance inspection for classes Q and V shall be in accordance with MIL-I-38535 including groups A, B, C, D, and E inspections and as specified herein except where option 2 of MIL-I-38535 permits alternate in-line control testing.
 - 4.4.1 Group A inspection.
 - a. Tests shall be as specified in table II herein.
 - b. For device class M, subgroups 7 and 8 tests shall be sufficient to verify the truth table. For device classes Q and V, subgroups 7 and 8 shall include verifying the functionality of the device; these tests shall have been fault graded in accordance with MIL-STD-883, test method 5012 (see 1.5 herein).
- 4.4.2 <u>Group C inspection</u>. The group C inspection end-point electrical parameters shall be as specified in table II herein.
 - 4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:
 - a. Test condition A, B, C or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005.
 - b. $T_{\Delta} = +125$ °C, minimum.
 - c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

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TABLE II. Electrical test requirements.

Test requirements	Subgroups (in accordance with MIL-STD-883, TM 5005, table 1)	Subgroups (in accordance with MIL-I-38535, table III)	
	Device class M	Device class Q	Device class V
Interim electrical parameters (see 4.2)	1	1	1
Final electrical parameters (see 4.2)	1, 2, 3, 7, 8, 9, <u>1</u> / 10, 11	1, 2, 3, 7, 8, 9, 10, 11 <u>1</u> /	1,2,3,7,8,9 <u>2</u> /10, 11
Group A test requirements (see 4.4)	1, 2, 3, 7, 8, 9, 10, 11	1, 2, 3, 7, 8 9, 10, 11	1,2,3,7,8 9, 10, 11
Group C end-point electrical parameters (see 4.4)	1, 2, 3	1, 2, 3	1, 2, 3
Group D end-point electrical parameters (see 4.4)	1, 2, 3	1, 2, 3	1, 2, 3
Group E end-point electrical parameters (see 4.4)	1	1	1

^{1/} PDA applies to subgroup 1.

- 4.4.2.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-I-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB, in accordance with MIL-I-38535, and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005.
- 4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table II herein.
- 4.4.4 Group E inspection. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein). RHA levels for device classes Q and V shall be M. D. L. R. F. G. and H and for device class M shall be M and D.
 - a. End-point electrical parameters shall be as specified in table II herein.
 - b. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-I-38535, appendix A, for the RHA level being tested. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-I-38535 for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at T_A = +25°C ±5°C, after exposure, to the subgroups specified in table II herein.
 - c. When specified in the purchase order or contract, a copy of the RHA delta limits shall be supplied.
 - 5. PACKAGING
- 5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-STD-883 (see 3.1 herein) for device class M and MIL-I-38535 for device classes Q and V.

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^{2/} PDA applies to subgroups 1 and 7.

6. NOTES

- 6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.
- 6.1.1 Replaceability. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
 - 6.1.2 Substitutability. Device class Q devices will replace device class M devices.
- 6.2 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-973 using DD Form 1692, Engineering Change Proposal.
- 6.3 <u>Record of users</u>. Military and industrial users shall inform Defense Electronics Supply Center when a system application requires configuration control and which SMD's are applicable to that system. DESC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DESC-EC, telephone (513) 296-6047.
- 6.4 <u>Comments</u>. Comments on this drawing should be directed to DESC-EC, Dayton, Ohio 45444-5765, or telephone (513) 296-8525.
- 6.5 <u>Abbreviations, symbols, and definitions</u>. The abbreviations, symbols, and definitions used herein are defined in MIL- $\overline{1}$ -38535 and MIL- \overline{STD} -1331.
- 6.6 One part one part number system. The one part one part number system described below has been developed to allow for transitions between identical generic devices covered by the three major microcircuit requirements documents (MIL-H-38534, MIL-I-38535, and 1.2.1 of MIL-STD-883) without the necessity for the generation of unique PIN's. The three military requirements documents represent different class levels, and previously when a device manufacturer upgraded military product from one class level to another, the benefits of the upgraded product were unavailable to the Original Equipment Manufacturer (OEM), that was contractually locked into the original unique PIN. By establishing a one part number system covering all three documents, the OEM can acquire to the highest class level available for a given generic device to meet system needs without modifying the original contract parts selection criteria.

Military documentation format	Example PIN under new system	Manufacturing source listing	Document <u>listing</u>
New MIL-H-38534 Standardized Military Drawings	5962-XXXXXZZ(H or K)YY	QML-38534	MIL-BUL-103
New MIL-I-38535 Standardized Military Drawings	5962-XXXXXZZ(Q or V)YY	QML-38535	MIL-BUL-103
New 1.2.1 of MIL-STD-883 Standardized Military Drawings	5962-XXXXXZZ(M)YY	MIL-BUL-103	MIL-BUL-103

6.7 Sources of supply.

- 6.7.1 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DESC-EC and have agreed to this drawing.
- 6.7.2 Approved sources of supply for device class M. Approved sources of supply for class M are listed in MIL-BUL-103. The vendors listed in MIL-BUL-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DESC-EC.

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